

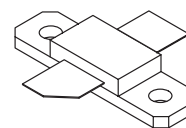
RF Power Field Effect Transistors N-Channel Enhancement-Mode Lateral MOSFETs

Designed for broadband commercial and industrial applications with frequencies up to 1000 MHz. The high gain and broadband performance of these devices make them ideal for large-signal, common-source amplifier applications in 28 volt base station equipment.

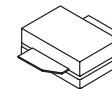
- Typical Two-Tone Performance at 945 MHz, 28 Volts
Output Power — 45 Watts PEP
Power Gain — 18.8 dB
Efficiency — 42%
IMD — -32 dBc
- Integrated ESD Protection
- Designed for Maximum Gain and Insertion Phase Flatness
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 945 MHz, 45 Watts CW Output Power
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- In Tape and Reel. R1 Suffix = 500 Units per 32 mm, 13 inch Reel.
- Low Gold Plating Thickness on Leads. L Suffix Indicates 40μ" Nominal.

MRF9045LR1
MRF9045LSR1

945 MHz, 45 W, 28 V
LATERAL N-CHANNEL
BROADBAND
RF POWER MOSFETs



CASE 360B-05, STYLE 1
NI-360
MRF9045LR1



CASE 360C-05, STYLE 1
NI-360S
MRF9045LSR1

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +15	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	125 0.71 175 1	W W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.4 1.0	$^\circ\text{C}/\text{W}$

Table 3. ESD Protection Characteristics

Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model	M1 (Minimum)

NOTE - CAUTION - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

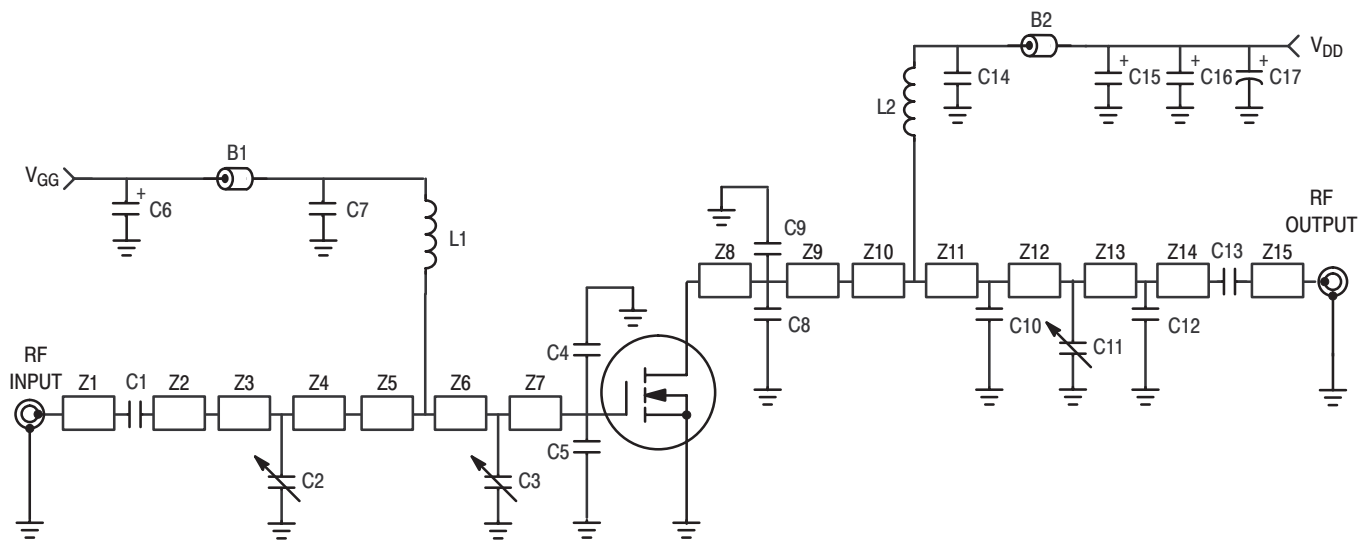
Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 65\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate–Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc
On Characteristics					
Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 150\ \mu\text{Adc}$)	$V_{GS(th)}$	2	3	4	Vdc
Gate Quiescent Voltage ($V_{DS} = 28\text{ Vdc}$, $I_D = 350\text{ mAdc}$)	$V_{GS(Q)}$	—	3.7	—	Vdc
Drain–Source On–Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 1\text{ Adc}$)	$V_{DS(on)}$	—	0.19	0.4	Vdc
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 3\text{ Adc}$)	g_{fs}	—	4	—	S
Dynamic Characteristics					
Input Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{iss}	—	69	—	pF
Output Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{oss}	—	37	—	pF
Reverse Transfer Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	1.5	—	pF

(continued)

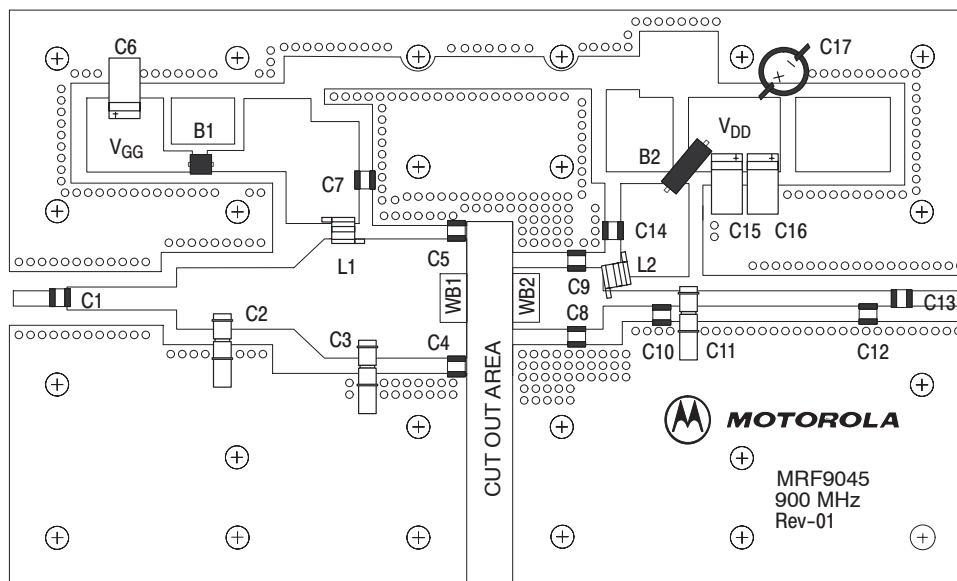
Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
Functional Tests (In Freescale Test Fixture, 50 ohm system)					
Two-Tone Common-Source Amplifier Power Gain ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 45\text{ W PEP}$, $I_{DQ} = 350\text{ mA}$, $f_1 = 945.0\text{ MHz}$, $f_2 = 945.1\text{ MHz}$)	G_{ps}	17	18.8	—	dB
Two-Tone Drain Efficiency ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 45\text{ W PEP}$, $I_{DQ} = 350\text{ mA}$, $f_1 = 945.0\text{ MHz}$, $f_2 = 945.1\text{ MHz}$)	η	38	42	—	%
3rd Order Intermodulation Distortion ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 45\text{ W PEP}$, $I_{DQ} = 350\text{ mA}$, $f_1 = 945.0\text{ MHz}$, $f_2 = 945.1\text{ MHz}$)	IMD	—	-32	-28	dBc
Input Return Loss ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 45\text{ W PEP}$, $I_{DQ} = 350\text{ mA}$, $f_1 = 945.0\text{ MHz}$, $f_2 = 945.1\text{ MHz}$)	IRL	—	-14	-9	dB
Two-Tone Common-Source Amplifier Power Gain ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 45\text{ W PEP}$, $I_{DQ} = 350\text{ mA}$, $f_1 = 930.0\text{ MHz}$, $f_2 = 930.1\text{ MHz}$ and $f_1 = 960.0\text{ MHz}$, $f_2 = 960.1\text{ MHz}$)	G_{ps}	—	18.5	—	dB
Two-Tone Drain Efficiency ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 45\text{ W PEP}$, $I_{DQ} = 350\text{ mA}$, $f_1 = 930.0\text{ MHz}$, $f_2 = 930.1\text{ MHz}$ and $f_1 = 960.0\text{ MHz}$, $f_2 = 960.1\text{ MHz}$)	η	—	41	—	%
3rd Order Intermodulation Distortion ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 45\text{ W PEP}$, $I_{DQ} = 350\text{ mA}$, $f_1 = 930.0\text{ MHz}$, $f_2 = 930.1\text{ MHz}$ and $f_1 = 960.0\text{ MHz}$, $f_2 = 960.1\text{ MHz}$)	IMD	—	-33	—	dBc
Input Return Loss ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 45\text{ W PEP}$, $I_{DQ} = 350\text{ mA}$, $f_1 = 930.0\text{ MHz}$, $f_2 = 930.1\text{ MHz}$ and $f_1 = 960.0\text{ MHz}$, $f_2 = 960.1\text{ MHz}$)	IRL	—	13	—	dB
Power Output, 1 dB Compression Point ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 45\text{ W CW}$, $I_{DQ} = 350\text{ mA}$, $f_1 = 945.0\text{ MHz}$)	P_{1dB}	—	55	—	W
Common-Source Amplifier Power Gain ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 45\text{ W CW}$, $I_{DQ} = 350\text{ mA}$, $f_1 = 945.0\text{ MHz}$)	G_{ps}	—	18	—	dB
Drain Efficiency ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 45\text{ W CW}$, $I_{DQ} = 350\text{ mA}$, $f_1 = 945.0\text{ MHz}$)	η	—	60	—	%
Output Mismatch Stress ($V_{DD} = 28\text{ Vdc}$, $P_{out} = 45\text{ W CW}$, $I_{DQ} = 350\text{ mA}$, $f = 945.0\text{ MHz}$, $V_{SWR} = 10:1$, All Phase Angles at Frequency of Tests)	Ψ	No Degradation In Output Power			



B1	Short Ferrite Bead Surface Mount	Z4	0.360" x 0.320" Microstrip
B2	Long Ferrite Bead Surface Mount	Z5	0.240" x 0.320" x 0.620", Taper
C1, C7, C13, C14	47 pF Chip Capacitors	Z6	0.140" x 0.620" Microstrip
C2, C3, C11	0.8–8.0 pF Gigatrim Variable Trim Capacitors	Z7	0.510" x 0.620" Microstrip
C4, C5, C8, C9	10 pF Chip Capacitors	Z8	0.330" x 0.320" Microstrip
C6, C15, C16	10 μ F, 35 V Tantalum Surface Mount Chip Capacitors	Z9	0.140" x 0.320" Microstrip
C10	2.2 pF Chip Capacitor	Z10	0.070" x 0.080" Microstrip
C12	0.7 pF Chip Capacitor – MRF9045LS	Z11	0.240" x 0.080" Microstrip
C17	220 μ F, 50 V Electrolytic Capacitor	Z12	0.140" x 0.080" Microstrip
L1, L2	12.5 nH Surface Mount Inductors, Coilcraft	Z13	0.930" x 0.080" Microstrip
Z1	0.260" x 0.080" Microstrip	Z14	0.180" x 0.080" Microstrip
Z2	0.610" x 0.120" Microstrip	Z15	0.350" x 0.080" Microstrip
Z3	0.260" x 0.320" Microstrip	PCB	Arlon GX-0300-55-22, 0.03", $\epsilon_r = 2.55$

Figure 1. 930 – 960 MHz Broadband Test Circuit Schematic



Freescale has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescale Semiconductor signature/logo. PCBs may have either Motorola or Freescale markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. 930 – 960 MHz Broadband Test Circuit Component Layout

TYPICAL CHARACTERISTICS

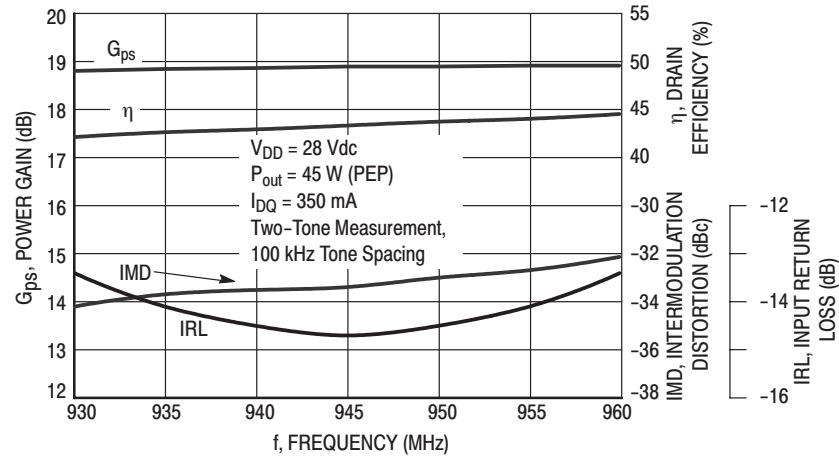


Figure 3. Class AB Broadband Circuit Performance

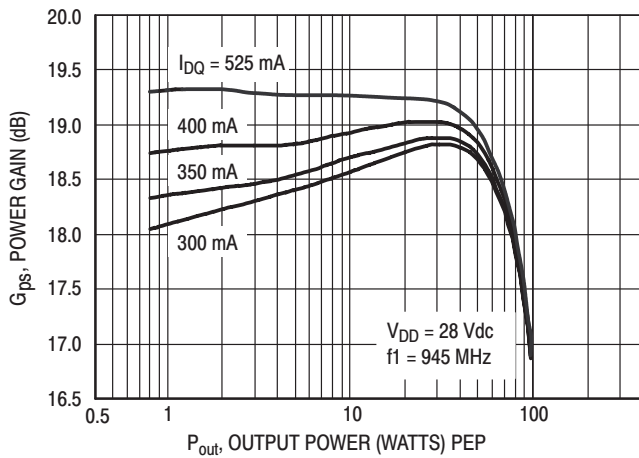


Figure 4. Power Gain versus Output Power

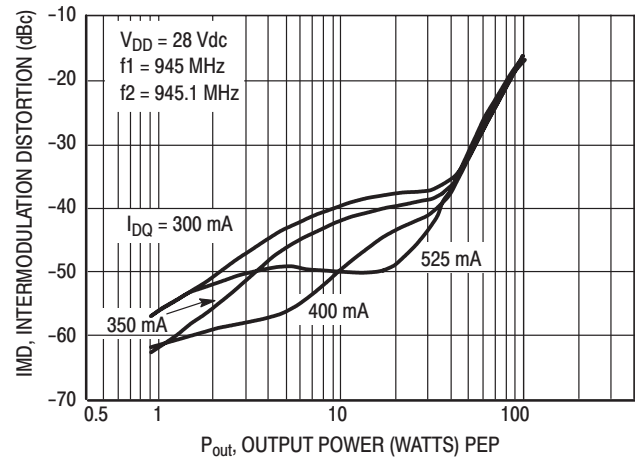


Figure 5. Intermodulation Distortion versus Output Power

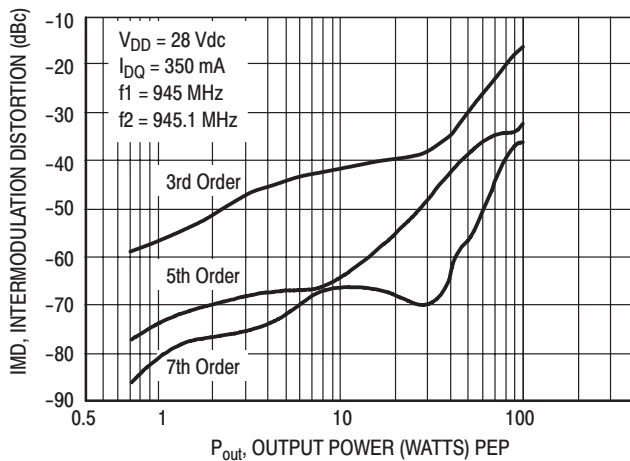


Figure 6. Intermodulation Distortion Products versus Output Power

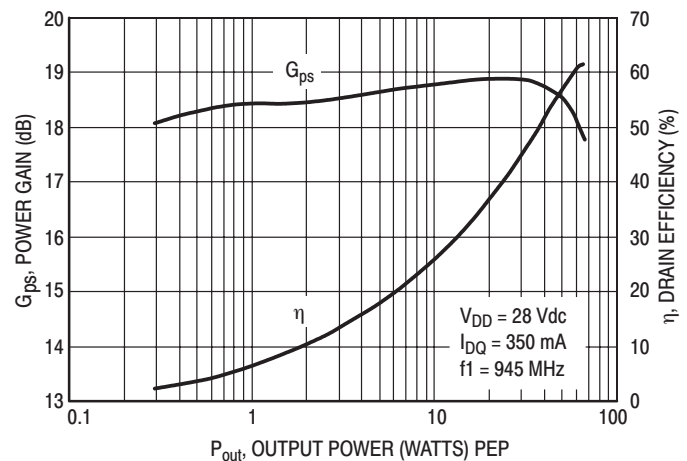
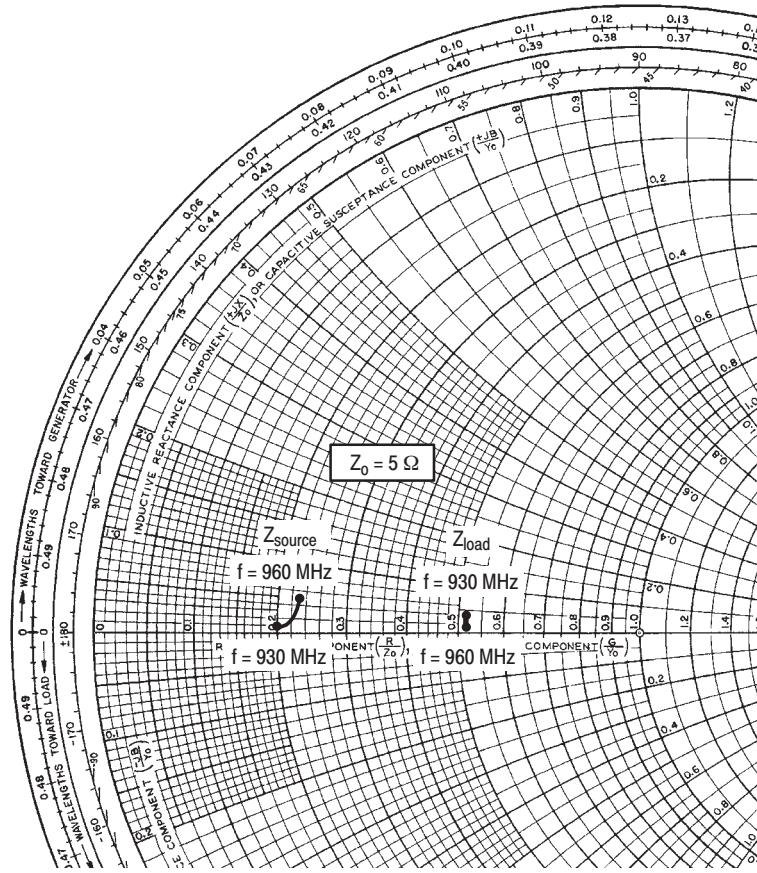


Figure 7. Power Gain, Efficiency versus Output Power

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$V_{DD} = 28\text{ V}$, $I_{DQ} = 350\text{ mA}$, $P_{out} = 45\text{ W PEP}$

f MHz	Z_{source} Ω	Z_{load} Ω
930	$1.02 + j0.06$	$2.6 + j0.20$
945	$1.10 + j0.11$	$2.6 + j0.16$
960	$1.15 + j0.25$	$2.6 + j0.10$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

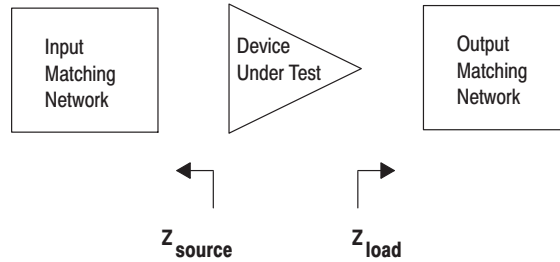
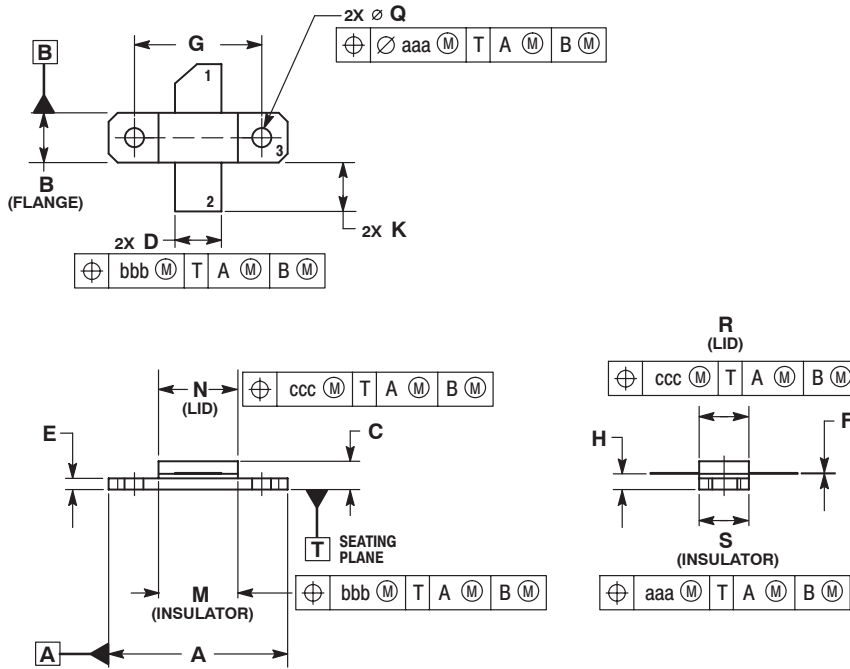


Figure 8. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS

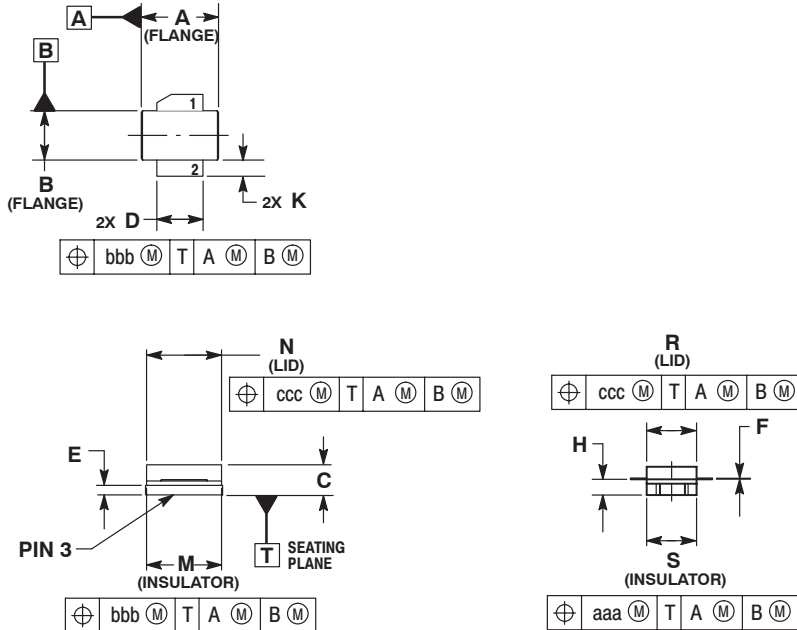


- NOTES:
1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.795	0.805	20.19	20.45
B	0.225	0.235	5.72	5.97
C	0.125	0.175	3.18	4.45
D	0.210	0.220	5.33	5.59
E	0.055	0.065	1.40	1.65
F	0.004	0.006	0.10	0.15
G	0.562 BSC		14.28 BSC	
H	0.077	0.087	1.96	2.21
K	0.220	0.250	5.59	6.35
M	0.355	0.365	9.02	9.27
N	0.357	0.363	9.07	9.22
Q	0.125	0.135	3.18	3.43
R	0.227	0.233	5.77	5.92
S	0.225	0.235	5.72	5.97
aaa	0.005 REF		0.13 REF	
bbb	0.010 REF		0.25 REF	
ccc	0.015 REF		0.38 REF	

- STYLE 1:
 PIN 1. DRAIN
 2. GATE
 3. SOURCE

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DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.375	0.385	9.53	9.78
B	0.225	0.235	5.72	5.97
C	0.105	0.155	2.67	3.94
D	0.210	0.220	5.33	5.59
E	0.035	0.045	0.89	1.14
F	0.004	0.006	0.10	0.15
H	0.057	0.067	1.45	1.70
K	0.085	0.115	2.16	2.92
M	0.355	0.365	9.02	9.27
N	0.357	0.363	9.07	9.22
R	0.227	0.23	5.77	5.92
S	0.225	0.235	5.72	5.97
aaa	0.005 REF		0.13 REF	
bbb	0.010 REF		0.25 REF	
ccc	0.015 REF		0.38 REF	

- STYLE 1:
 PIN 1. DRAIN
 2. GATE
 3. SOURCE

CASE 360C-05 ISSUE D NI-360S MRF9045LSR1

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